

60V P-Channel Enhancement Mode MOSFET

Voltage

-60 V

Current

-4.2 A

Features

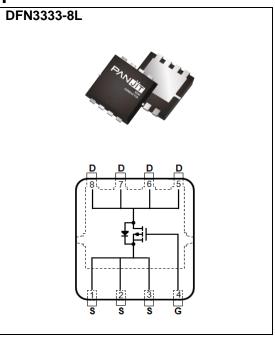
- $R_{DS(ON)}$, $V_{GS}@-10V$, $I_D@-6A<68m\Omega$
- R_{DS(ON)}, V_{GS}@-4.5V, I_D@-3A<85mΩ
- Advanced Trench Process Technology
- High density cell design for ultra low on-resistance
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

• Case: DFN3333-8L Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.03 grams



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V _{DS}	-60	V	
Gate-Source Voltage		V _{GS}	<u>+</u> 20		
Continuous Drain Current(Note 4)	T _A =25°C	I _D	-4.2		
	T _A =70°C		-3.4	Α	
Pulsed Drain Current ^(Note 1)		I _{DM}	-16.8	<u> </u>	
Power Dissipation	T _A =25°C	PD	2.1	W	
	T _A =70°C		1.3		
Operating Junction and Storage Temperature Range		T _J ,T _{STG}	-55~150	°C	
Typical Thermal Resistance Junction to Ambient ^(Note 4,5)		R _{θJA}	59.5	°C/W	

Limited only By Maximum Junction Temperature



Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =-250uA	-60	-	-	V	
Gate Threshold Voltage	$V_{GS(th)}$	V _{DS} =V _{GS} , I _D =-250uA	-1	-1.53	-2.5		
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =-10V, I _D =-6A	-	55	68	0	
		V _{GS} =-4.5V, I _D =-3A	-	71	85	mΩ	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-60V, V _{GS} =0V	-	-	-1	uA	
Gate-Source Leakage Current	I _{GSS}	V _{GS} = <u>+</u> 20V, V _{DS} =0V	-	-	<u>+</u> 100	nA	
Dynamic ^(Note 6)							
Total Gate Charge	Q_g	V _{DS} =-30V, I _D =-6A, V _{GS} =-10V ^(Note 3)	-	17	-	nC	
Gate-Source Charge	Q_{gs}		-	2.8	-		
Gate-Drain Charge	Q_gd		-	3.6	-		
Input Capacitance	Ciss	V _{DS} =-30V, V _{GS} =0V, f=1MHZ	-	879	-	pF	
Output Capacitance	Coss		-	70	-		
Reverse Transfer Capacitance	Crss		-	47	-		
Turn-On Delay Time	td _(on)	V_{DD} =-30V, I_{D} =-1A, V_{GS} =-10V, R_{G} =6 Ω (Note 3)	-	8.4	-		
Turn-On Rise Time	t _r		-	30	-	ns	
Turn-Off Delay Time	td _(off)		-	52	-		
Turn-Off Fall Time	t _f		-	16	-		
Drain-Source Diode							
Maximum Continuous Drain-Source	I.		-	-	-4.2	А	
Diode Forward Current	I _S						
Diode Forward Voltage	V_{SD}	I _S =-1A, V _{GS} =0V	-	-0.73	-1	V	

NOTES:

- 1. Pulse width<300us, Duty cycle<2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$ =150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.
- 4. The maximum current rating is package limited.
- 5. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. Guaranteed by design, not subject to production testing.



TYPICAL CHARACTERISTIC CURVES

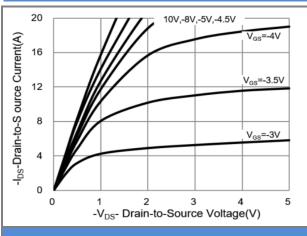


Fig.1 On-Region Characteristics

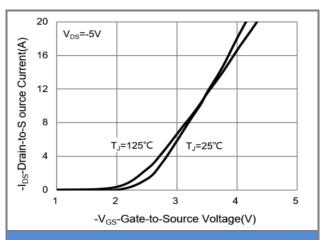


Fig.2 Transfer Characteristics

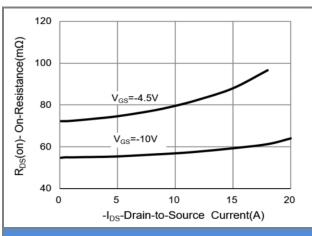


Fig.3 On-Resistance vs. Drain Current

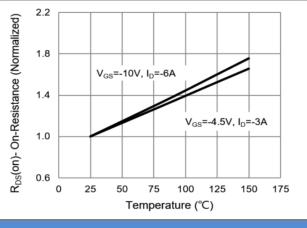
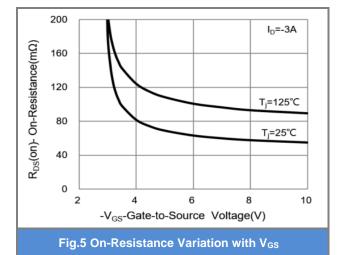


Fig.4 On-Resistance vs. Junction temperature



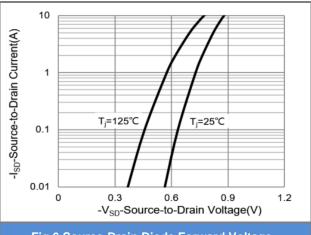


Fig.6 Source-Drain Diode Forward Voltage



1.2

1.0

8.0

0.6

0.4

25

V_{TH}-Gate-to-Source Vriance

PJQ4463AP-AU

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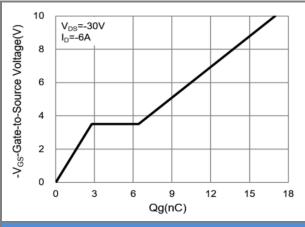
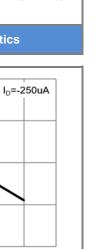


Fig.7 Gate-Charge Characteristics



175

Fig.9 Threshold Voltage Variation with Temperature

75

Temperature (°C)

100

125

150

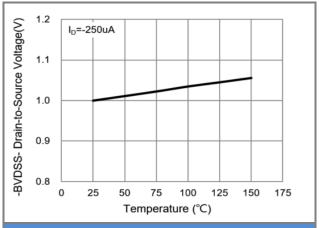


Fig.8 Breakdown Voltage Variation vs. Temperature

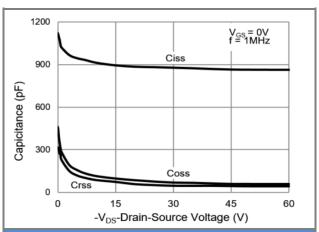


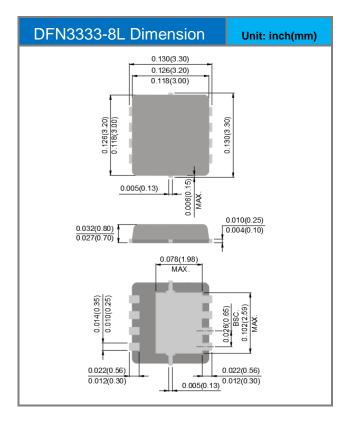
Fig.10 Capacitance vs. Drain-Source Voltage

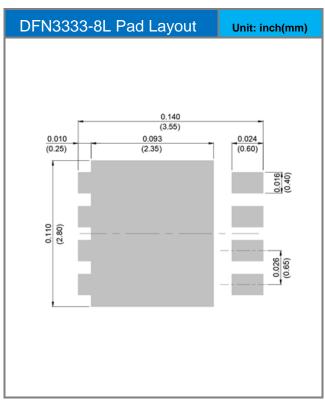


Product and Packing Information

Part No.	Package Type	Packing Type	Marking	
PJQ4463AP-AU	DFN3333-8L	5K pcs / 13" reel	4463	

Packaging Information & Mounting Pad Layout







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